
AMENDMENTS TO THE CLAIMS:

Please add new claims 109 and 110 as shown on the following pages. Material inserted is indicated by underlining (insertion) and material deleted is indicated by strike-out (~~deletion~~).

1. (Original) A CVD process for forming a thin film, comprising:
 - a vaporizing step of heating and vaporizing an organometallic compound to yield a source gas;
 - a thin film forming step of introducing said source gas onto a substrate and allowing the source gas to react on a surface of the substrate to yield a thin film of a metal or metal oxide;
 - a recovering step of cooling an exhaust gas containing a reaction product formed in said thin film forming step and an unreacted source gas to condense or solidify said unreacted source gas to thereby yield a recovered content containing a liquid or solid organometallic compound; and
 - a purifying step of separating and purifying the organometallic compound from said recovered content.

2. (Original) A CVD process for forming a thin film according to claim 1, further comprising a step of eliminating oxygen from the exhaust gas prior to the recovering step.

3. (Original) A CVD process for forming a thin film according to claim 1, wherein said recovering step is performed by cooling the exhaust gas with a cold trap and wherein oxygen has been eliminated from said cold trap.
4. (Original) A CVD process for forming a thin film according to claim 2, wherein said recovering step is performed by cooling the exhaust gas with a cold trap and wherein oxygen has been eliminated from said cold trap.
5. (Original) A CVD process for forming a thin film according to claim 1, wherein said purifying step comprises a step of distilling the recovered content to thereby separate the organometallic compound.
6. (Original) A CVD process for forming a thin film according to claim 2, wherein said purifying step comprises a step of distilling the recovered content to thereby separate the organometallic compound.
7. (Original) A CVD process for forming a thin film according to claim 3, wherein said purifying step comprises a step of distilling the recovered content to thereby separate the organometallic compound.

8. (Original) A CVD process for forming a thin film according to claim 4, wherein said purifying step comprises a step of distilling the recovered content to thereby separate the organometallic compound.
9. (Original) A CVD process for forming a thin film according to claim 1, wherein said purifying step comprises a step of bringing the recovered content into contact with a solvent in which the organometallic compound is soluble.
10. (Original) A CVD process for forming a thin film according to claim 2, wherein said purifying step comprises a step of bringing the recovered content into contact with a solvent in which the organometallic compound is soluble.
11. (Original) A CVD process for forming a thin film according to claim 3, wherein said purifying step comprises a step of bringing the recovered content into contact with a solvent in which the organometallic compound is soluble.
12. (Original) A CVD process for forming a thin film according to claim 4, wherein said purifying step comprises a step of bringing the recovered content into contact with a solvent in which the organometallic compound is soluble.

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13. (Original) A CVD process for forming a thin film according to claim 5, wherein said purifying step comprises a step of bringing the recovered content into contact with a solvent in which the organometallic compound is soluble.
 14. (Original) A CVD process for forming a thin film according to claim 6, wherein said purifying step comprises a step of bringing the recovered content into contact with a solvent in which the organometallic compound is soluble.
 15. (Original) A CVD process for forming a thin film according to claim 7, wherein said purifying step comprises a step of bringing the recovered content into contact with a solvent in which the organometallic compound is soluble.
 16. (Original) A CVD process for forming a thin film according to claim 8, wherein said purifying step comprises a step of bringing the recovered content into contact with a solvent in which the organometallic compound is soluble.
 17. (Original) A CVD process for forming a thin film according to claim 9, wherein said purifying step comprises a step of eliminating oxygen from the solvent in which the organometallic compound is soluble prior to contact between the recovered content and the solvent.

18. (Original) A CVD process for forming a thin film according to claim 10, wherein said purifying step comprises a step of eliminating oxygen from the solvent in which the organometallic compound is soluble prior to contact between the recovered content and the solvent.
19. (Original) A CVD process for forming a thin film according to claim 11, wherein said purifying step comprises a step of eliminating oxygen from the solvent in which the organometallic compound is soluble prior to contact between the recovered content and the solvent.
20. (Original) A CVD process for forming a thin film according to claim 12, wherein said purifying step comprises a step of eliminating oxygen from the solvent in which the organometallic compound is soluble prior to contact between the recovered content and the solvent.
21. (Original) A CVD process for forming a thin film according to claim 13, wherein said purifying step comprises a step of eliminating oxygen from the solvent in which the organometallic compound is soluble prior to contact between the recovered content and the solvent.
22. (Original) A CVD process for forming a thin film according to claim 14, wherein said purifying step comprises a step of eliminating oxygen from the solvent in which the

organometallic compound is soluble prior to contact between the recovered content and the solvent.

23. (Original) A CVD process for forming a thin film according to claim 15, wherein said purifying step comprises a step of eliminating oxygen from the solvent in which the organometallic compound is soluble prior to contact between the recovered content and the solvent.
24. (Original) A CVD process for forming a thin film according to claim 16, wherein said purifying step comprises a step of eliminating oxygen from the solvent in which the organometallic compound is soluble prior to contact between the recovered content and the solvent.
25. (Original) A CVD process for forming a thin film according to claim 9, wherein said purifying step comprises one of a step of cooling a solvent containing the recovered content to thereby separate the organometallic compound in a solid state, and a step of mixing a solvent containing the recovered content with a poor solvent to thereby separate the organometallic compound in a solid state, the organometallic compound being sparingly soluble in said poor solvent.
26. (Original) A CVD process for forming a thin film according to claim 10, wherein said purifying step comprises one of a step of cooling a solvent containing the recovered

content to thereby separate the organometallic compound in a solid state, and a step of mixing a solvent containing the recovered content with a poor solvent to thereby separate the organometallic compound in a solid state, the organometallic compound being sparingly soluble in said poor solvent.

27. (Original) A CVD process for forming a thin film according to claim 11, wherein said purifying step comprises one of a step of cooling a solvent containing the recovered content to thereby separate the organometallic compound in a solid state, and a step of mixing a solvent containing the recovered content with a poor solvent to thereby separate the organometallic compound in a solid state, the organometallic compound being sparingly soluble in said poor solvent.
28. (Original) A CVD process for forming a thin film according to claim 12, wherein said purifying step comprises one of a step of cooling a solvent containing the recovered content to thereby separate the organometallic compound in a solid state, and a step of mixing a solvent containing the recovered content with a poor solvent to thereby separate the organometallic compound in a solid state, the organometallic compound being sparingly soluble in said poor solvent.
29. (Original) A CVD process for forming a thin film according to claim 13, wherein said purifying step comprises one of a step of cooling a solvent containing the recovered content to thereby separate the organometallic compound in a solid state, and a step of

mixing a solvent containing the recovered content with a poor solvent to thereby separate the organometallic compound in a solid state, the organometallic compound being sparingly soluble in said poor solvent.

30. (Original) A CVD process for forming a thin film according to claim 14, wherein said purifying step comprises one of a step of cooling a solvent containing the recovered content to thereby separate the organometallic compound in a solid state, and a step of mixing a solvent containing the recovered content with a poor solvent to thereby separate the organometallic compound in a solid state, the organometallic compound being sparingly soluble in said poor solvent.
31. (Original) A CVD process for forming a thin film according to claim 15, wherein said purifying step comprises one of a step of cooling a solvent containing the recovered content to thereby separate the organometallic compound in a solid state, and a step of mixing a solvent containing the recovered content with a poor solvent to thereby separate the organometallic compound in a solid state, the organometallic compound being sparingly soluble in said poor solvent.
32. (Original) A CVD process for forming a thin film according to claim 16, wherein said purifying step comprises one of a step of cooling a solvent containing the recovered content to thereby separate the organometallic compound in a solid state, and a step of mixing a solvent containing the recovered content with a poor solvent to thereby separate

the organometallic compound in a solid state, the organometallic compound being sparingly soluble in said poor solvent.

33. (Original) A CVD process for forming a thin film according to claim 17, wherein said purifying step comprises one of a step of cooling a solvent containing the recovered content to thereby separate the organometallic compound in a solid state, and a step of mixing a solvent containing the recovered content with a poor solvent to thereby separate the organometallic compound in a solid state, the organometallic compound being sparingly soluble in said poor solvent.
34. (Original) A CVD process for forming a thin film according to claim 18, wherein said purifying step comprises one of a step of cooling a solvent containing the recovered content to thereby separate the organometallic compound in a solid state, and a step of mixing a solvent containing the recovered content with a poor solvent to thereby separate the organometallic compound in a solid state, the organometallic compound being sparingly soluble in said poor solvent.
35. (Original) A CVD process for forming a thin film according to claim 19, wherein said purifying step comprises one of a step of cooling a solvent containing the recovered content to thereby separate the organometallic compound in a solid state, and a step of mixing a solvent containing the recovered content with a poor solvent to thereby separate

the organometallic compound in a solid state, the organometallic compound being sparingly soluble in said poor solvent.

36. (Original) A CVD process for forming a thin film according to claim 20, wherein said purifying step comprises one of a step of cooling a solvent containing the recovered content to thereby separate the organometallic compound in a solid state, and a step of mixing a solvent containing the recovered content with a poor solvent to thereby separate the organometallic compound in a solid state, the organometallic compound being sparingly soluble in said poor solvent.
37. (Original) A CVD process for forming a thin film according to claim 21, wherein said purifying step comprises one of a step of cooling a solvent containing the recovered content to thereby separate the organometallic compound in a solid state, and a step of mixing a solvent containing the recovered content with a poor solvent to thereby separate the organometallic compound in a solid state, the organometallic compound being sparingly soluble in said poor solvent.
38. (Original) A CVD process for forming a thin film according to claim 22, wherein said purifying step comprises one of a step of cooling a solvent containing the recovered content to thereby separate the organometallic compound in a solid state, and a step of mixing a solvent containing the recovered content with a poor solvent to thereby separate

the organometallic compound in a solid state, the organometallic compound being sparingly soluble in said poor solvent.

39. (Original) A CVD process for forming a thin film according to claim 23, wherein said purifying step comprises one of a step of cooling a solvent containing the recovered content to thereby separate the organometallic compound in a solid state, and a step of mixing a solvent containing the recovered content with a poor solvent to thereby separate the organometallic compound in a solid state, the organometallic compound being sparingly soluble in said poor solvent.
40. (Original) A CVD process for forming a thin film according to claim 24, wherein said purifying step comprises one of a step of cooling a solvent containing the recovered content to thereby separate the organometallic compound in a solid state, and a step of mixing a solvent containing the recovered content with a poor solvent to thereby separate the organometallic compound in a solid state, the organometallic compound being sparingly soluble in said poor solvent.
41. (Original) A CVD process for forming a thin film according to claim 25, wherein said purifying step further comprises a step of heating the separated solid organometallic compound to thereby sublimate one of the organometallic compound and the reaction product.

42. (Original) A CVD process for forming a thin film according to claim 26, wherein said purifying step further comprises a step of heating the separated solid organometallic compound to thereby sublime one of the organometallic compound and the reaction product.
43. (Original) A CVD process for forming a thin film according to claim 27, wherein said purifying step further comprises a step of heating the separated solid organometallic compound to thereby sublime one of the organometallic compound and the reaction product.
44. (Original) A CVD process for forming a thin film according to claim 28, wherein said purifying step further comprises a step of heating the separated solid organometallic compound to thereby sublime one of the organometallic compound and the reaction product.
45. (Original) A CVD process for forming a thin film according to claim 29, wherein said purifying step further comprises a step of heating the separated solid organometallic compound to thereby sublime one of the organometallic compound and the reaction product.
46. (Original) A CVD process for forming a thin film according to claim 30, wherein said purifying step further comprises a step of heating the separated solid organometallic

compound to thereby sublime one of the organometallic compound and the reaction product.

47. (Original) A CVD process for forming a thin film according to claim 31, wherein said purifying step further comprises a step of heating the separated solid organometallic compound to thereby sublime one of the organometallic compound and the reaction product.

48. (Original) A CVD process for forming a thin film according to claim 32, wherein said purifying step further comprises a step of heating the separated solid organometallic compound to thereby sublime one of the organometallic compound and the reaction product.

49. (Original) A CVD process for forming a thin film according to claim 33, wherein said purifying step further comprises a step of heating the separated solid organometallic compound to thereby sublime one of the organometallic compound and the reaction product.

50. (Original) A CVD process for forming a thin film according to claim 34, wherein said purifying step further comprises a step of heating the separated solid organometallic compound to thereby sublime one of the organometallic compound and the reaction product.

51. (Original) A CVD process for forming a thin film according to claim 35, wherein said purifying step further comprises a step of heating the separated solid organometallic compound to thereby sublime one of the organometallic compound and the reaction product.
52. (Original) A CVD process for forming a thin film according to claim 36, wherein said purifying step further comprises a step of heating the separated solid organometallic compound to thereby sublime one of the organometallic compound and the reaction product.
53. (Original) A CVD process for forming a thin film according to claim 37, wherein said purifying step further comprises a step of heating the separated solid organometallic compound to thereby sublime one of the organometallic compound and the reaction product.
54. (Original) A CVD process for forming a thin film according to claim 38, wherein said purifying step further comprises a step of heating the separated solid organometallic compound to thereby sublime one of the organometallic compound and the reaction product.

55. (Original) A CVD process for forming a thin film according to claim 39, wherein said purifying step further comprises a step of heating the separated solid organometallic compound to thereby sublime one of the organometallic compound and the reaction product.
56. (Original) A CVD process for forming a thin film according to claim 40, wherein said purifying step further comprises a step of heating the separated solid organometallic compound to thereby sublime one of the organometallic compound and the reaction product.
57. (Withdrawn) A CVD process for forming a thin film comprising: a vaporizing step of heating and vaporizing an organometallic compound to yield a source gas;
a thin-film-forming step of introducing said source gas onto a substrate and allowing the source gas to react on a surface of the substrate to yield a thin film of a metal or metal oxide;
a recovering step of bringing an exhaust gas containing a reaction product formed in said thin-film-forming step and an unreacted source gas into contact with a solvent in which the organometallic compound is soluble to dissolve the organometallic compound in the solvent to thereby recover the organometallic compound; and
a purifying step of separating and purifying the organometallic compound from the solvent containing the organometallic compound.

58. (Withdrawn) A CVD process for forming a thin film according to claim 57, further comprising a step of eliminating oxygen from the exhaust gas prior to the recovering step.
59. (Withdrawn) A CVD process for forming a thin film according to claim 57, wherein said recovering step comprises a step of eliminating oxygen from the solvent in which the organometallic compound is soluble prior to contact between the exhaust gas and the solvent.
60. (Withdrawn) A CVD process for forming a thin film according to claim 58, wherein said recovering step comprises a step of eliminating oxygen from the solvent in which the organometallic compound is soluble prior to contact between the exhaust gas and the solvent.
61. (Withdrawn) A CVD process for forming a thin film according to claim 57, wherein said purifying step comprises one of a step of cooling the solvent to thereby separate the organometallic compound in a solid state and a step of bringing the solvent into contact with a poor solvent to thereby separate the organometallic compound in a solid state, the organometallic compound being sparingly soluble in said poor solvent.
62. (Withdrawn) A CVD process for forming a thin film according to claim 58, wherein said purifying step comprises one of a step of cooling the solvent to thereby separate the organometallic compound in a solid state and a step of bringing the solvent into contact

with a poor solvent to thereby separate the organometallic compound in a solid state, the organometallic compound being sparingly soluble in said poor solvent.

63. (Withdrawn) A CVD process for forming a thin film according to claim 59, wherein said purifying step comprises one of a step of cooling the solvent to thereby separate the organometallic compound in a solid state and a step of bringing the solvent into contact with a poor solvent to thereby separate the organometallic compound in a solid state, the organometallic compound being sparingly soluble in said poor solvent.
64. (Withdrawn) A CVD process for forming a thin film according to claim 60, wherein said purifying step comprises one of a step of cooling the solvent to thereby separate the organometallic compound in a solid state and a step of bringing the solvent into contact with a poor solvent to thereby separate the organometallic compound in a solid state, the organometallic compound being sparingly soluble in said poor solvent.
65. (Withdrawn) A CVD process for forming a thin film according to claim 61, wherein said purifying step further comprises a step of heating the solid organometallic compound to thereby sublime one of the organometallic compound and the reaction product.
66. (Withdrawn) A CVD process for forming a thin film according to claim 62, wherein said purifying step further comprises a step of heating the solid organometallic compound to thereby sublime one of the organometallic compound and the reaction product.

67. (Withdrawn) A CVD process for forming a thin film according to claim 63, wherein said purifying step further comprises a step of heating the solid organometallic compound to thereby sublime one of the organometallic compound and the reaction product.
68. (Withdrawn) A CVD process for forming a thin film according to claim 64, wherein said purifying step further comprises a step of heating the solid organometallic compound to thereby sublime one of the organometallic compound and the reaction product.
69. (Withdrawn) A CVD process for forming a thin film according to claim 57, wherein said purifying step comprises a step of subjecting the solvent containing the organometallic compound to liquid chromatography.
70. (Withdrawn) A CVD process for forming a thin film according to claim 58, wherein said purifying step comprises a step of subjecting the solvent containing the organometallic compound to liquid chromatography.
71. (Withdrawn) A CVD process for forming a thin film according to claim 59, wherein said purifying step comprises a step of subjecting the solvent containing the organometallic compound to liquid chromatography.

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72. (Withdrawn) A CVD process for forming a thin film according to claim 60, wherein said purifying step comprises a step of subjecting the solvent containing the organometallic compound to liquid chromatography.
73. (Withdrawn) A CVD process for forming a thin film according to claim 69, wherein a filler used in the liquid chromatograph is one selected from the group consisting of silica gel, octadecylsilane, alumina, porous polymers, graphite carbon, and zeolite.
74. (Withdrawn) A CVD process for forming a thin film according to claim 70, wherein a filler used in the liquid chromatograph is one selected from the group consisting of silica gel, octadecylsilane, alumina, porous polymers, graphite carbon, and zeolite.
75. (Withdrawn) A CVD process for forming a thin film according to claim 71, wherein a filler used in the liquid chromatograph is one selected from the group consisting of silica gel, octadecylsilane, alumina, porous polymers, graphite carbon, and zeolite.
76. (Withdrawn) A CVD process for forming a thin film according to claim 72, wherein a filler used in the liquid chromatograph is one selected from the group consisting of silica gel, octadecylsilane, alumina, porous polymers, graphite carbon, and zeolite.
77. (Withdrawn) A CVD process for forming a thin film, comprising: a vaporizing step of heating and vaporizing an organometallic compound to yield a source gas;

a thin-film-forming step of introducing said source gas onto a substrate and allowing the source gas to react on a surface of the substrate to yield a thin film of a metal or metal oxide;

a recovering step of bringing an exhaust gas containing a reaction product formed in said thin film forming step and

an unreacted source gas into contact with an adsorbent to adsorb the organometallic compound to thereby recover the organometallic compound; and

a purifying step of separating and purifying the organometallic compound from the adsorbent adsorbing the organometallic compound.

78. (Withdrawn) A CVD process for forming a thin film according to claim 77, further comprising a step of eliminating oxygen from the exhaust gas prior to the recovering step.
79. (Withdrawn) A CVD process for forming a thin film according to claim 77, wherein an activated carbon is used as the adsorbent.
80. (Withdrawn) A CVD process for forming a thin film according to claim 78, wherein an activated carbon is used as the adsorbent.
81. (Withdrawn) A CVD process for forming a thin film according to claim 77, wherein a host compound capable of including the organometallic compound as a guest is used as the adsorbent.

82. (Withdrawn) A CVD process for forming a thin film according to claim 78, wherein a host compound capable of including the organometallic compound as a guest is used as the adsorbent.
83. (Withdrawn) A CVD process for forming a thin film according to claim 77, wherein said purifying step comprises a step of heating the adsorbent adsorbing the organometallic compound to thereby separate the organometallic compound.
84. (Withdrawn) A CVD process for forming a thin film according to claim 78, wherein said purifying step comprises a step of heating the adsorbent adsorbing the organometallic compound to thereby separate the organometallic compound.
85. (Withdrawn) A CVD process for forming a thin film according to claim 79, wherein said purifying step comprises a step of heating the adsorbent adsorbing the organometallic compound to thereby separate the organometallic compound.
86. (Withdrawn) A CVD process for forming a thin film according to claim 80, wherein said purifying step comprises a step of heating the adsorbent adsorbing the organometallic compound to thereby separate the organometallic compound.

87. (Withdrawn) A CVD process for forming a thin film according to claim 81, wherein said purifying step comprises a step of heating the adsorbent adsorbing the organometallic compound to thereby separate the organometallic compound.
88. (Withdrawn) A CVD process for forming a thin film according to claim 82, wherein said purifying step comprises a step of heating the adsorbent adsorbing the organometallic compound to thereby separate the organometallic compound.
89. (Withdrawn) A CVD process for forming a thin film according to claim 83, wherein said purifying step further comprises a step of subjecting the separated organometallic compound to gas chromatography.
90. (Withdrawn) A CVD process for forming a thin film according to claim 84, wherein said purifying step further comprises a step of subjecting the separated organometallic compound to gas chromatography.
91. (Withdrawn) A CVD process for forming a thin film according to claim 85, wherein said purifying step further comprises a step of subjecting the separated organometallic compound to gas chromatography.

92. (Withdrawn) CVD process for forming a thin film according to claim 86, wherein said purifying step further comprises a step of subjecting the separated organometallic compound to gas chromatography.
93. (Withdrawn) A CVD process for forming a thin film according to claim 87, wherein said purifying step further comprises a step of subjecting the separated organometallic compound to gas chromatography.
94. (Withdrawn) A CVD process for forming a thin film according to claim 88, wherein said purifying step further comprises a step of subjecting the separated organometallic compound to gas chromatography.
95. (Withdrawn) A CVD process for forming a thin film according to claim 89, wherein a filler used in the gas chromatograph is one selected from the group consisting of siloxanes, silicagel, octadecylsilane, alumina, porous polymers, graphite carbon, and zeolite.
96. (Withdrawn) A CVD process for forming a thin film according to claim 90, wherein a filler used in the gas chromatograph is one selected from the group consisting of siloxanes, silicagel, octadecylsilane, alumina, porous polymers, graphite carbon, and zeolite.

97. (Withdrawn) A CVD process for forming a thin film according to claim 91, wherein a filler used in the gas chromatograph is one selected from the group consisting of siloxanes, silica gel, octadecylsilane, alumina, porous polymers, graphite carbon, and zeolite.
98. (Withdrawn) A CVD process for forming a thin film according to claim 92, wherein a filler used in the gas chromatograph is one selected from the group consisting of siloxanes, silicagel, octadecylsilane, alumina, porous polymers, graphite carbon, and zeolite.
99. (Withdrawn) A CVD process for forming a thin film according to claim 93, wherein a filler used in the gas chromatograph is one selected from the group consisting of siloxanes, silicagel, octadecylsilane, alumina, porous polymers, graphite carbon, and zeolite.
100. (Withdrawn) A CVD process for forming a thin film according to claim 94, wherein a filler used in the gas chromatograph is one selected from the group consisting of siloxanes, silica gel, octadecylsilane, alumina, porous polymers, graphite carbon, and zeolite.
101. (Withdrawn) A CVD apparatus for producing a thin film comprising a container for accommodating an organometallic compound as a material, a heating means for heating

the solution to thereby vaporize the organometallic compound to yield a source gas, and a reactor for allowing said source gas to react to thereby form a thin film of a metal or metaloxide on a substrate,

wherein said apparatus further comprises, on the downstream side from the reactor, a recovering means for obtaining a recovered content containing the organometallic compound from an exhaust gas, said exhaust gas being composed of a reaction product formed through a reaction and an unreacted source gas, and a purifying means for separating and purifying the organometallic compound from said recovered content.

102. (Withdrawn) A CVD apparatus for producing a thin film according to claim 101, further comprising, between the reactor and the recovering means, an oxygen eliminating means for eliminating oxygen from the exhaust gas.
103. (Withdrawn) A CVD apparatus for producing a thin film according to claim 101, wherein said recovering means is a cold trap in which the exhaust gas is cooled to yield the recovered content in a liquid state.
104. (Withdrawn) A CVD apparatus for producing a thin film according to claim 102, wherein said recovering means is a cold trap in which the exhaust gas is cooled to yield the recovered content in a liquid state.

105. (Withdrawn) A CVD apparatus for producing a thin film according to claim 101, wherein said recovering means is a solvent tank for containing a solvent in which the organometallic compound is soluble.
106. (Withdrawn) A CVD apparatus for producing a thin film according to claim 102, wherein said recovering means is a solvent tank for containing a solvent in which the organometallic compound is soluble.
107. (Withdrawn) A CVD apparatus for producing a thin film according to claim 101, wherein said recovering means is an adsorption tank filled with an adsorbent capable of adsorbing the organometallic compound.
108. (Withdrawn) A CVD apparatus for producing a thin film according to claim 102, wherein said recovering means is an adsorption tank filled with an adsorbent capable of adsorbing the organometallic compound.
109. (New) A CVD process according to claim 1, wherein the organometallic compound is of a metal selected from the group consisting of copper, indium, tantalum, tungsten, molybdenum, titanium, and rhenium.

110. (New) A CVD process according to claim 1, wherein the organometallic compound is of a metal selected from the group consisting of silver, gold, platinum, urthenium, rhodium, indium or osminum.